

# ROITHNER LASERTECHNIK

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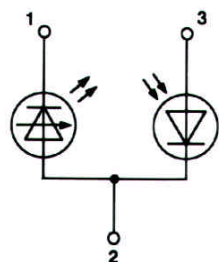
## S6510MG TECHNICAL DATA



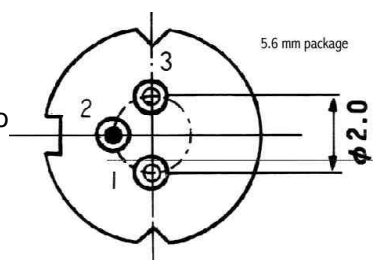
### Visible Wavelength Laserdiode

Structure **InGaAlP**, index guided single transverse mode  
 Lasing wavelength **655nm typ.**  
 Output power **10 mW, CW**  
 Package **5.6 mm MG, TO-18**

#### PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



#### Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	$P_o$	10	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operation Case Temperature	$T_c$	-10 .. +60	°C
Storage Temperature	$T_{STG}$	-40 .. +85	°C

#### Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	$I_{th}$			15	20	mA
Operation Current	$I_{op}$	$P_o = 10mW$		26	40	mA
Operating Voltage	$V_{op}$	$P_o = 10mW$		2.2	2.6	V
Lasing Wavelength	$\lambda_p$	$P_o = 10mW$	650	655	660	nm
Beam Divergence	$\theta_{//}$	$P_o = 10mW$	5	7	9	°
Beam Divergence	$\theta_{\perp}$	$P_o = 10mW$	30	32	38	°
Slope Efficiency	$\eta$		0.5	0.7	1	mW/mA
Monitor Current	$I_m$	$P_o = 10mW$	50	200	500	$\mu A$